

AMENDMENTS TO THE CLAIMS:

Please cancel claims 15-26. The remaining claims are listed below.

1. A method of operating a memory system having a plurality of memory cells organized into a plurality of blocks that individually contain the smallest group of memory cells that are simultaneously erasable by addressing individual blocks, said blocks being individually programmable in units of an integer number of a plurality of pages of a given amount of data per page, comprising programming sectors of data individually containing less than said given amount of data across boundaries of said pages within individual blocks, wherein more sectors of data are programmed into a block than a number of pages in the block.

2. The method of claim 1, wherein said sectors of data individually contain all of user data, data of attributes of the user data and data of attributes of the block in which said sectors of data are programmed.

3. The method of claim 1, wherein said sectors of data individually contain both user data and data of attributes of the user data, with data of attributes of the block in which said sectors of data are programmed being stored as part of different data sectors.

4. The method of claim 1, wherein said sectors of data individually contain user data, with data of attributes of the user data and data of attributes of the block in which the individual sectors of data are being programmed being stored as part of different data sectors.

5. The method of either one of claims 3 or 4, wherein said different data sectors are stored in different blocks than said sectors of data to which the data of attributes pertains.

6. The method of any one of claims 1-4, additionally comprising operating the memory cells with a plurality of effective threshold levels in excess of two that correspond to a plurality of alterable states of the individual cells in excess of two, whereby storage elements of the cells individually store more than one bit of data.

7. A method of operating a memory system having a plurality of memory cells organized into a plurality of blocks that individually contain the smallest group of memory cells that are simultaneously erasable by addressing individual blocks, said blocks being individually programmable in units of one or more integer numbers of a pages of a given amount of data per page, comprising programming sectors of data individually containing more than said given amount of data across boundaries of said pages.

8. The method of claim 7, wherein said sectors of data individually contain all of user data, data of attributes of the user data and data of attributes of the block in which said sectors of data are programmed.

9. The method of claim 7, wherein said sectors of data individually contain both user data and data of attributes of the user data, with data of attributes of the block in which said sectors of data are programmed being stored as part of different data sectors.

10. The method of claim 7, wherein said sectors of data individually contain user data, with data of attributes of the user data and data of attributes of the block in which the individual sectors of data are being programmed being stored as part of different data sectors.

11. The method of either one of claims 9 or 10, wherein said different data sectors are stored in different blocks than said sectors of data to which the data of attributes pertains.

12. The method of any one of claims 7-10, wherein said blocks individually include only one page.

13. The method of any one of claims 7-10, wherein said blocks individually include a plurality of pages.

14. The method of any one of claims 7-10, additionally comprising operating the memory cells with a plurality of effective threshold levels in excess of two that correspond to a plurality of alterable states of the individual cells in excess of two, whereby storage elements of the cells individually store more than one bit of data.

15.-26. (Cancelled)